

GAU2823

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Application of : Rhodes et. al ✓
Applicants : Rhodes et. al ✓
Serial No. : 09/008,531 ✓
Filed : 01/16/98 ✓
Title : METHOD OF MAKING A SEMICONDUCTOR DEVICE HAVING
IMPROVED CONTACTS TO A THIN CONDUCTIVE LAYER
Docket No. : MIO0012V2
Examiner : EATON
Art Unit : 2823

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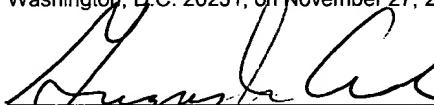
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CERTIFICATE OF MAILING

I hereby certify that this correspondence is being deposited with the United States Postal Service as first class mail in an envelope addressed to: Assistant Commissioner for Patents, Washington, D.C. 20231, on November 27, 2000


Gregory J. Adams

44,494
Reg. No.

Sir:

AMENDMENT AND RESPONSE

This paper is being filed in response to the Office Action mailed October 24, 2000. Reconsideration of the present application is respectfully requested in light of the remarks and amendments below.

IN THE SPECIFICATION

The Examiner has objected to the title of the invention. At page 1, please amend the title to "METHOD OF MAKING A SEMICONDUCTOR DEVICE HAVING IMPROVED CONTACTS".

IN THE CLAIMS

21. (Amended) A process for making a semiconductor device comprising the steps of:
providing a substrate having at least one semiconductor layer;
forming an underlayer over the at least one semiconductor layer;